

NVTFS5826NL

Power MOSFET

60 V, 24 mΩ, 20 A, Single N-Channel

Features

- Small Footprint (3.3 x 3.3 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- NVTFS5826NLWF – Wettable Flanks Product
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	60	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current $R_{\Psi J-mb}$ (Notes 1, 2, 3, 4)	Steady State	$T_{mb} = 25^{\circ}\text{C}$	I_D	20	A
		$T_{mb} = 100^{\circ}\text{C}$		14	
Power Dissipation $R_{\Psi J-mb}$ (Notes 1, 2, 3)		$T_{mb} = 25^{\circ}\text{C}$	P_D	22	W
		$T_{mb} = 100^{\circ}\text{C}$		11	
Continuous Drain Current $R_{\theta JA}$ (Notes 1 & 3, 4)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	7.6	A
		$T_A = 100^{\circ}\text{C}$		5.4	
Power Dissipation $R_{\theta JA}$ (Notes 1, 3)		$T_A = 25^{\circ}\text{C}$	P_D	3.2	W
		$T_A = 100^{\circ}\text{C}$		1.6	
Pulsed Drain Current	$T_A = 25^{\circ}\text{C}$, $t_p = 10\text{ }\mu\text{s}$		I_{DM}	127	A
Operating Junction and Storage Temperature			T_J , T_{stg}	-55 to +175	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	18	A
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^{\circ}\text{C}$, $V_{DD} = 24\text{ V}$, $V_{GS} = 10\text{ V}$, $I_{L(pk)} = 20\text{ A}$, $L = 0.1\text{ mH}$, $R_G = 25\text{ }\Omega$)			E_{AS}	20	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Junction-to-Mounting Board (top) – Steady State (Note 2 and 3)	$R_{\Psi J-mb}$	6.8	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	47	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51-12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
4. Continuous DC current rating. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

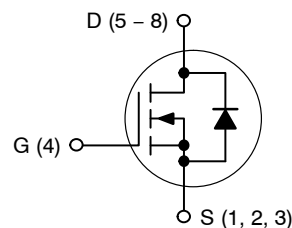


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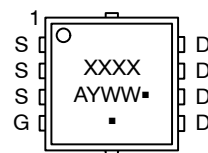
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)} \text{ MAX}$	$I_D \text{ MAX}$
60 V	24 mΩ @ 10 V	20 A
	32 mΩ @ 4.5 V	

N-Channel



MARKING DIAGRAM



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 60 V	T _J = 25°C		1.0	μA
			T _J = 125°C		10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.5		2.5	V
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A		19	24	mΩ
		V _{GS} = 4.5 V, I _D = 10 A		25	32	
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 5 A		8		S

CHARGES AND CAPACITANCES

Input Capacitance	C _{iss}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 25 V		850		pF
Output Capacitance	C _{oss}			85		
Reverse Transfer Capacitance	C _{rss}			50		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 48 V, I _D = 10 A		8.3		nC
Threshold Gate Charge	Q _{G(TH)}			1		
Gate-to-Source Charge	Q _{GS}			3		
Gate-to-Drain Charge	Q _{GD}			4		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 48 V, I _D = 10 A		16		nC

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 4.5 V, V _{DS} = 48 V, I _D = 10 A		9		ns
Rise Time	t _r			29		
Turn-Off Delay Time	t _{d(off)}			14		
Fall Time	t _f			21		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 10 A	T _J = 25°C		0.8	1.2	V
			T _J = 125°C		0.7		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 10 A			18		ns
Charge Time	t _a				14		
Discharge Time	t _b				4		
Reverse Recovery Charge	Q _{RR}				17		nC

5. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

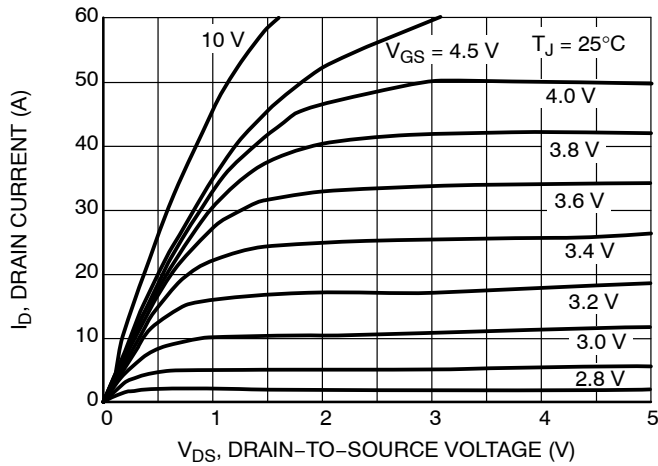


Figure 1. On-Region Characteristics

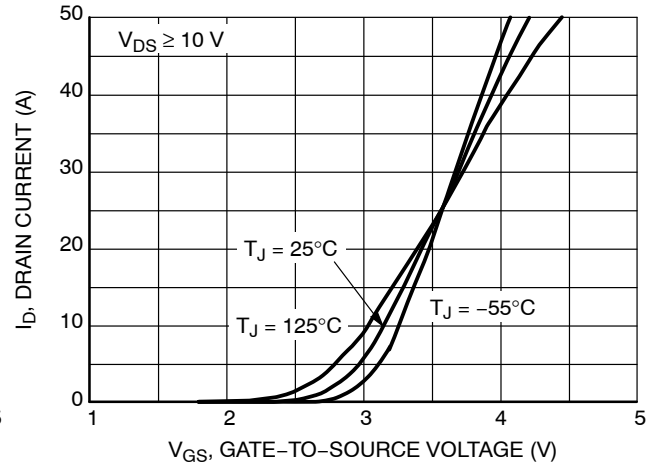


Figure 2. Transfer Characteristics

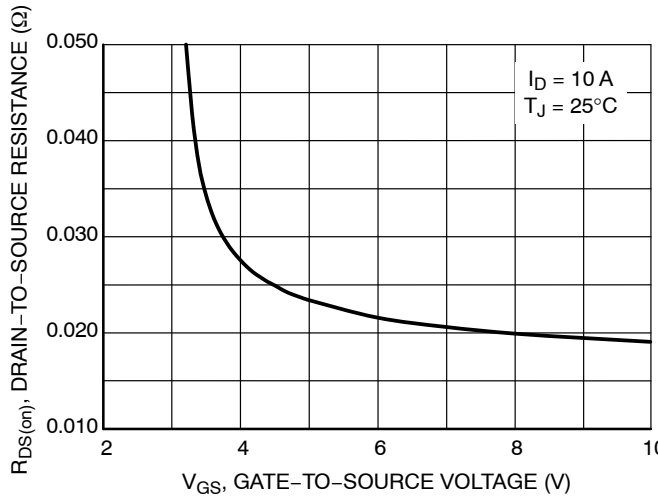


Figure 3. On-Resistance vs. Gate-to-Source Voltage

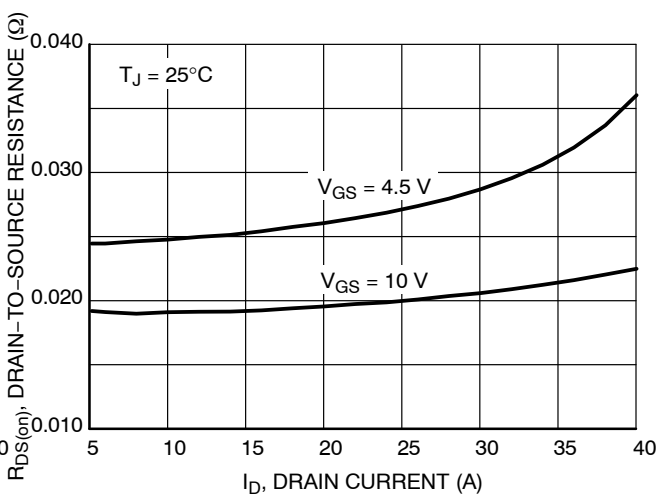


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

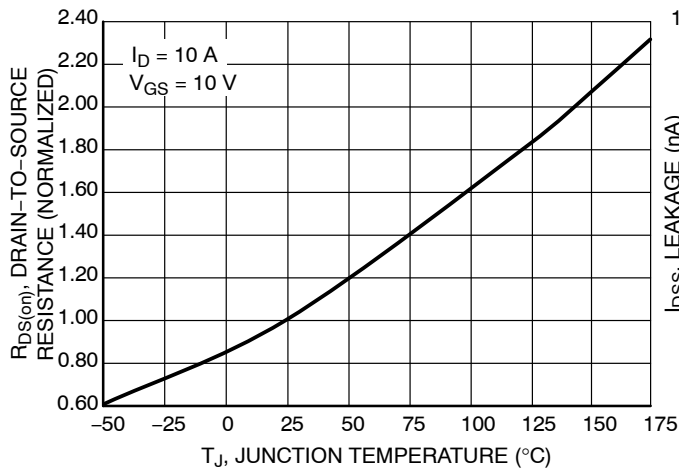


Figure 5. On-Resistance Variation with Temperature

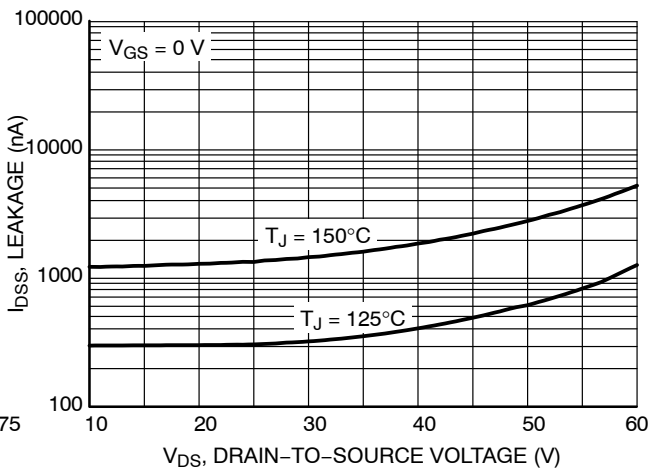


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

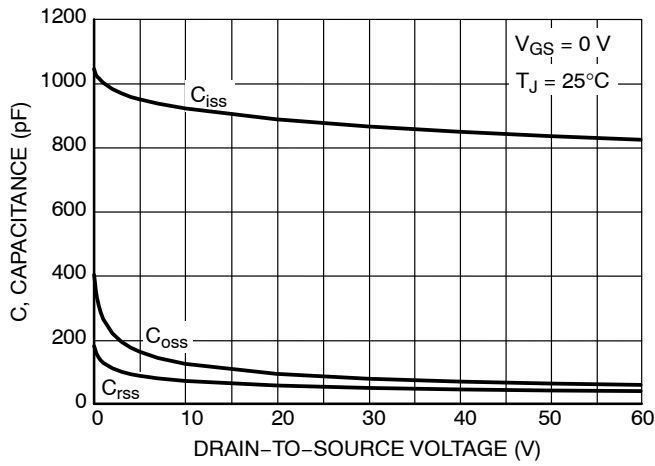


Figure 7. Capacitance Variation

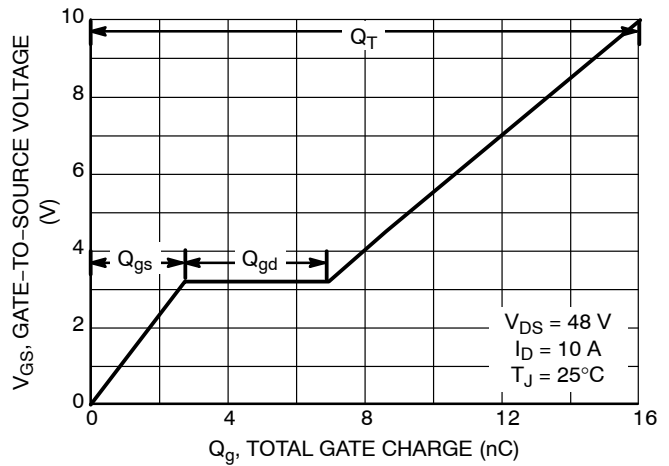


Figure 8. Gate-to-Source Voltage vs. Total Charge

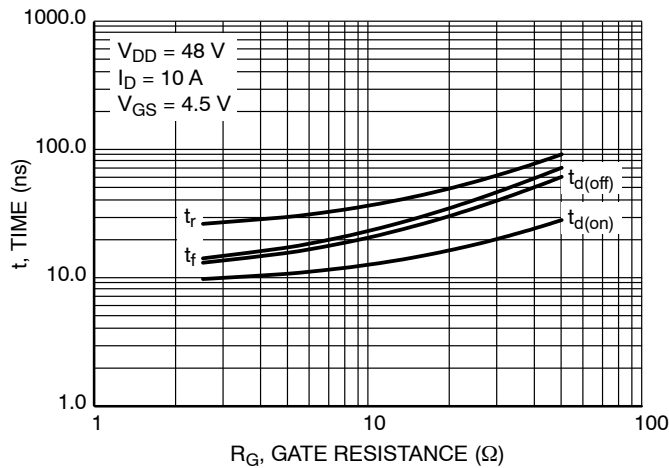


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

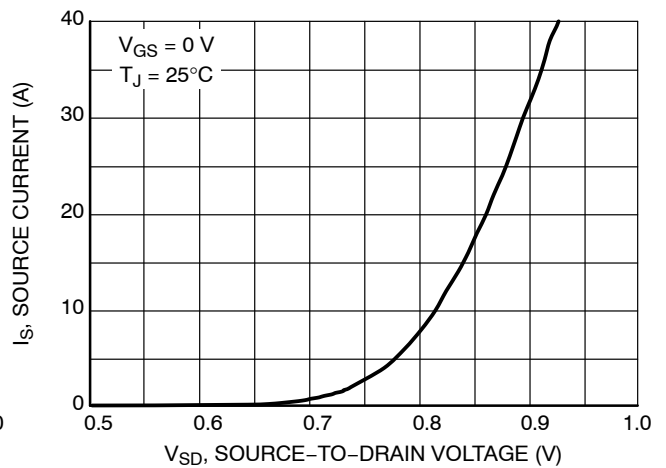


Figure 10. Diode Forward Voltage vs. Current

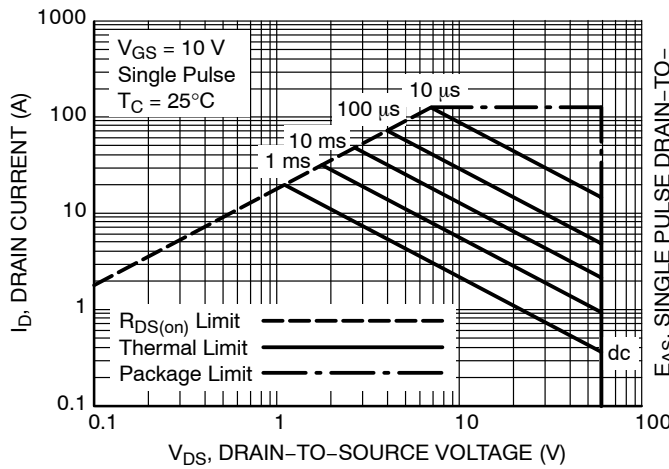


Figure 11. Maximum Rated Forward Biased Safe Operating Area

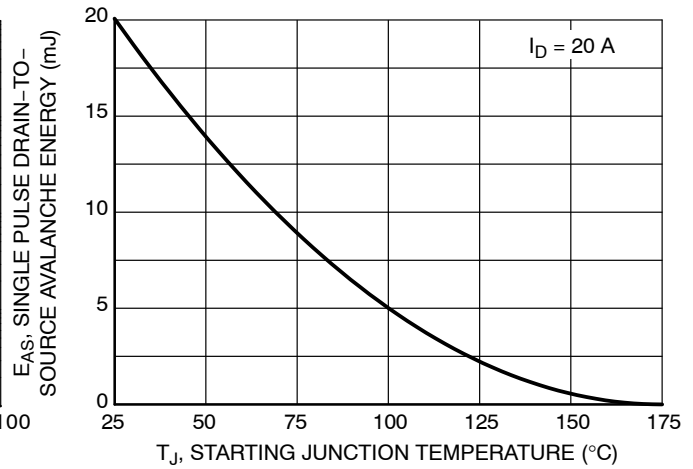


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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TYPICAL CHARACTERISTICS

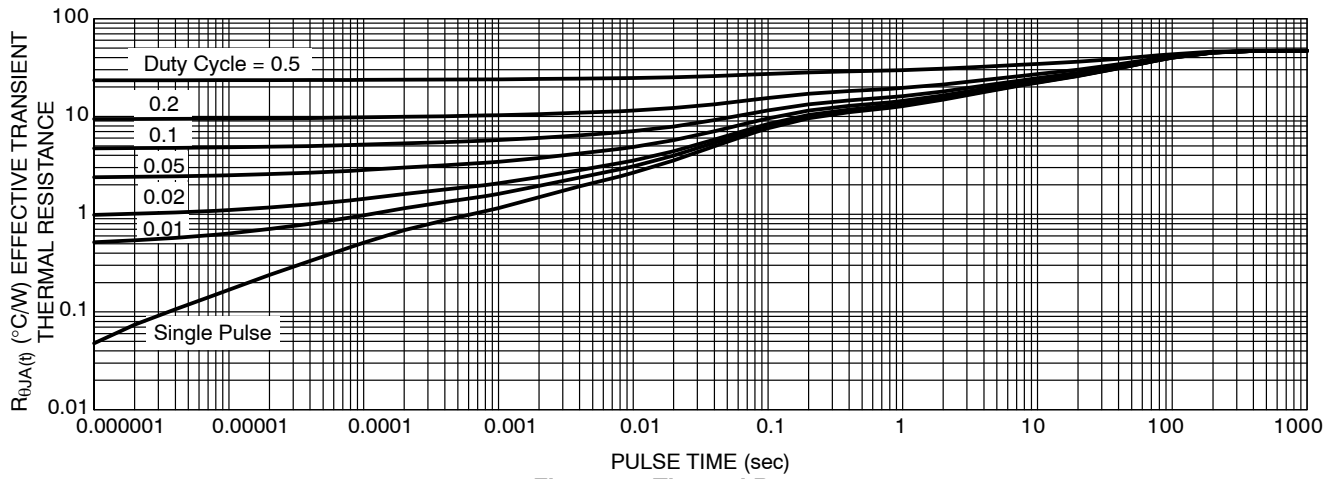


Figure 13. Thermal Response

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVTFS5826NLTAG	5826	WDFN8 (Pb-Free)	1500 / Tape & Reel
NVTFS5826NLWFTAG	26LW	WDFN8 (Pb-Free)	1500 / Tape & Reel
NVTFS5826NLTWG	5826	WDFN8 (Pb-Free)	5000 / Tape & Reel
NVTFS5826NLWFTWG	26LW	WDFN8 (Pb-Free)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

